TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7WG126FU,TC7WG126FK

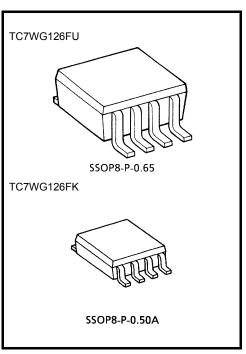
Dual Bus Buffer with 3-STATE Output

Features

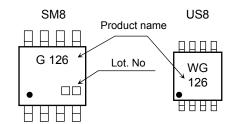
- High-level output current: I_{OH}/I_{OL} = ±8 mA (min) at V_{CC} = 3 V
- High-speed operation: t_{pd} = 2.5 ns (typ.)

at V_{CC} = 3.3 V,15pF

- Operating voltage range: V_{CC} = 0.9~3.6 V
- 5.5-V tolerant inputs
- 3.6-V power down protection outputs



Marking



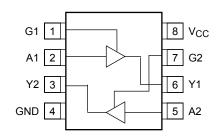
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Value	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	VIN	-0.5~7.0	V	
DC output voltage	Vour	-0.5~4.6 (Note 1)	V	
De oulput voltage	VOUT	-0.5~V _{CC} + 0.5 (Note 2)	v	
Input diode current	I _{IK}	-20	mA	
Output diode current	I _{ОК}	-20 (Note 3)	mA	
DC output current	IOUT	±25	mA	
DC V _{CC} / ground current	Icc	±100	mA	
Power dissipation	PD	300 (SM8) 200 (US8)	mW	
Storage temperature	T _{stg}	-65~150	°C	



SSOP8-P-0.65 : 0.02 g (typ.) SSOP8-P-0.50A : 0.01 g (typ.)

Pin Assignment (top view)



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: $V_{CC} = 0V$

Note 2: High or Low State. I_{OUT} absolute maximum rating must be observed. Note 3: $V_{OUT} < GND$

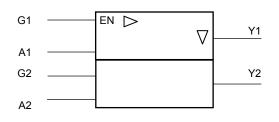
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Truth Table

Inp	uts	Outputs			
G	А	Y			
L	Х	Z			
Н	L	L			
Н	Н	Н			
X: Don't Care					

Z: High impedance

IEC Logic Symbol



Operating Ranges

Characteristics	Symbol	Value	Unit
Power supply voltage	V _{CC}	0.9~3.6	V
Input voltage	V _{IN}	0~5.5	V
Output voltage		0~3.6 (Note 4)	V
	Vout	0~V _{CC} (Note 5)	v
		±8.0 (Note 6)	
		±4.0 (Note 7)	
Output Ourrent	±3.0 (Not		mA
Output Current	IOH/IOL	±1.7 (Note 9)	ma
		±0.3 (Note 10)	
		±0.02 (Note 11)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dV	0~10 (Note 12)	ns/V

- Note 4: $V_{CC} = 0V$
- Note 5: High or Low state
- Note 6: V_{CC} = 3.0~3.6 V
- Note 7: V_{CC} = 2.3~2.7 V
- Note 8: V_{CC} = 1.65~1.95 V
- Note 9: V_{CC} = 1.4~1.6 V
- Note 10: V_{CC} = 1.1~1.3 V
- Note 11: V_{CC} = 0.9 V
- Note 12: V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

Electrical Characteristics

DC Characteristics

Characteristics		Symbol	Tost	Condition		7	Га = 25°С)	Ta = -4	0~85°C	Unit					
		Symbol	Test	Condition	V _{CC} (V)	Min	Тур.	Max	Min	Max	Onit					
					0.9	V _{CC}	_	_	V _{CC}	_						
						V _{CC} × 0.7			- V _{CC} -							
	High level	VIH		_	1.4~1.6	V _{CC} × 0.65	_	_	V _{CC} × 0.65	_						
					1.65~ 1.95	V _{CC} × 0.65	_		V _{CC} × 0.65	_						
					2.3~2.7	1.7			1.7	_						
Input voltage					3.0~3.6	2.0	_	_	2.0	_	v					
input voltage					0.9	—	_	GND	—	GND	v					
					1.1~1.3		_	$V_{CC} \times 0.3$		$\begin{array}{c} V_{CC} \\ \times \ 0.3 \end{array}$						
	Low level	VIL		_	1.4~1.6	_	_	V _{CC} × 0.35	_	V _{CC} × 0.35						
					1.65~ 1.95	_	_	V _{CC} × 0.35	_	V _{CC} × 0.35						
						_	_	0.7	_	0.7						
									3.0~3.6	_	_	0.8	_	0.8		
						I _{OH} =-0.02 mA	0.9	0.75	_	_	0.75	_				
			-	I _{OH} = -0.3 mA	1.1~1.3	V _{CC} × 0.75			V _{CC} × 0.75	_	_					
	High level	V _{ОН}		V _{IN} =V _{IH}	I _{OH} = -1.7 mA	1.4~1.6	V _{CC} × 0.75	_	_	V _{CC} × 0.75	_					
				I _{OH} = -3.0 mA	1.65~ 1.95	V _{CC} -0.45			V _{CC} -0.45							
				I _{OH} = -4.0 mA	2.3~2.7	2.0			2.0							
Output voltage									I _{OH} = -8.0 mA	3.0~3.6	2.48			2.48		V
Output voltage				I _{OL} = 0.02 mA	0.9	_		0.1	_	0.1	v					
				I _{OL} = 0.3 mA	1.1~1.3	—		$\begin{array}{c} V_{CC} \\ \times \ 0.25 \end{array}$	—	$\begin{array}{c} V_{CC} \\ \times \ 0.25 \end{array}$						
	Low level	V _{OL}	V _{IN} = V _{IL} or VIH	I _{OL} = 1.7 mA	1.4~1.6	_		V _{CC} × 0.25	_	V _{CC} × 0.25						
			or VIH	I _{OL} = 3.0 mA	1.65~ 1.95	_		0.45	_	0.45						
				I _{OL} = 4.0 mA	2.3~2.7	—		0.4	_	0.4						
			I _{OL} = 8.0 mA	3.0~3.6	—		0.4	—	0.4							
Input leakage current		I _{IN}	V _{IN} = 0~5	5.5V	0~3.6		_	±0.1		±1.0	μA					
3-state output off-s	tate current	I _{OZ}	V _{IN} = V _{IH} V _{OUT} = 0	or V _{IL} ~3.6V	0.9~3.6			1.0		10.0	μΑ					
Power off leakage	current	I _{OFF}	V _{IN} = 5.5 or V _{OUT} =	/ = 3.6V	0.0	_		1.0	_	10.0	μΑ					
Quiescent supply of	current	ICC	$V_{IN} = V_{CO}$	c or GND	3.6	_	_	1.0	_	10.0	μA					

AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Tost Condition		Ta = 25°C	2	Ta = -4	0~85°C	Unit	
Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit	
		0.9 — 1	18.3	_		_				
			1.1~1.3		9.4	18.4	1.0	34.9		
		C _L = 10 pF,	1.4~1.6		5.5	8.5	1.0	10.7		
		$R_{L} = 1 M\Omega$	1.65~ 1.95		4.2	6.2	1.0	6.7		
			2.3~2.7		2.8	3.9	1.0	4.4		
			3.0~3.6		2.3	3.1	1.0	3.7		
			0.9	_	21.2	_		_		
			1.1~1.3	_	10.7	21.5	1.0	38.0		
Propagation delay time	t _{pLH}	C _L = 15 pF,	1.4~1.6	_	6.1	9.3	1.0	11.9	20	
Propagation delay time	t _{pHL}	$R_{L} = 1 M\Omega$	1.65~ 1.95	_	4.7	6.9	1.0	7.1	ns	
			2.3~2.7		3.1	4.4	1.0	5.0		
			3.0~3.6	_	2.5	3.4	1.0	3.9		
			0.9	_	30.5			_		
			1.1~1.3	_	14.9	30.0	1.0	58.1		
		$\begin{array}{l} C_L=30 \text{ pF},\\ R_L=1 \text{ M}\Omega \end{array}$	1.4~1.6	_	8.2	13.2	1.0	16.6		
			1.65~ 1.95	_	6.1	9.2	1.0	9.9		
			2.3~2.7	_	4.1	5.7	1.0	6.1		
			3.0~3.6	_	3.4	4.4	1.0	4.8		
		$\begin{array}{l} C_L = 10 \text{ pF}, \\ R_L = 100 \text{ k}\Omega \end{array}$	0.9	_	24.0	_	_	_		
				1.1~1.3	_	11.8	22.5	1.0	35.8	
			1.4~1.6		6.8	10.4	1.0	12.0		
		$C_L = 10 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95	_	5.1	7.3	1.0	8.1		
		-	2.3~2.7		3.4	4.6	1.0	5.3		
			3.0~3.6	_	2.5	3.4	1.0	3.9		
		$\begin{array}{l} C_L = 15 \text{ pF}, \\ R_L = 100 \text{ k}\Omega \end{array}$	0.9		26.6	_	_	_		
			1.1~1.3		13.0	25.0	1.0	41.9		
Output enable time	t _{pZL}		1.4~1.6	_	7.4	11.4	1.0	13.4	ns	
	t _{pZH}	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95		5.5	7.9	1.0	8.5		
			2.3~2.7		3.7	4.9	1.0	5.5		
			3.0~3.6	_	3.0	4.1	1.0	4.6		
		$\begin{array}{l} C_L=30 \ pF, \\ R_L=100 \ k\Omega \end{array}$	0.9	_	36.4	_	_	_		
			1.1~1.3	_	17.9	35.8	1.0	59.1		
			1.4~1.6		9.8	15.3	1.0	17.8		
		$C_L = 30 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95		7.2	10.5	1.0	11.2		
			2.3~2.7	_	4.5	5.9	1.0	6.6		
			3.0~3.6		3.6	4.6	1.0	5.3		

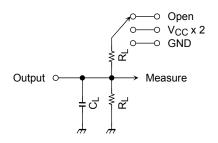
Characteristics	Symbol	Test Condition		٦	Га = 25°С	2	Ta = -4	0~85°C	Unit						
Characteristics	Symbol	Test Condition	$V_{CC}(V)$	(V) Min Typ. Max Min		Min	Max	Offic							
		$C_L = 10 \text{ pF},$ $R_L = 100 \text{ k}\Omega$	0.9	_	168.6	_	_	_							
			1.1~1.3	_	9.5	18.4	1.0	25.2							
			1.4~1.6	_	7.5	9.5	1.0	10.6							
		$C_L = 10 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95	_	7.1	8.7	1.0	9.6							
		-	2.3~2.7	_	6.8	7.9	1.0	8.8							
			3.0~3.6	_	6.5	7.5	1.0	8.4							
	t _{pLZ} t _{pHZ}	$\begin{array}{l} C_L = 15 \text{ pF}, \\ R_L = 100 \text{ k}\Omega \end{array}$	0.9	_	201.8		_	_							
		$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.1~1.3	_	10.5	19.8	1.0	27.6	ns						
Output disable time			1.4~1.6	_	9.0	10.4	1.0	12.3							
			$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95	_	8.5	9.7	1.0	10.6				
								-	_	_	-	2.3~2.7	_	7.9	8.8
			3.0~3.6	_	7.6	8.3	1.0	9.5							
		$\begin{array}{l} C_L=30 \text{ pF},\\ R_L=100 \text{ k}\Omega \end{array}$	0.9	_	251.5	_	_	_							
			1.1~1.3	_	14.1	23.8	1.0	31.9							
			1.4~1.6	_	13.5	14.5	1.0	16.0							
		$C_{L} = 30 \text{ pF},$ $B_{L} = 5 \text{ kO}$	$C_L = 30 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95	_	12.7	14.3	1.0	15.0						
				_	12.2	14.1	1.0	14.7							
			3.0~3.6	_	11.9	13.8	1.0	14.4							
Input capacitance	C _{IN}	—	3.6	_	3	_	_		pF						
Power dissipation capacitance	C _{PD}	(Note 13)	0.9 ~ 3.6		10				pF						

Note 13:C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

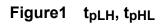
Average operating current can be obtained by the equation:

 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$

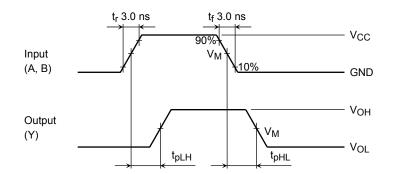
AC Characteristics Measurement Circuit

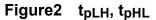


Characteristics	Switch
t _{pLH} , t _{pHL}	Open
t _{pLZ} , t _{pZL}	V _{CC} x 2
^t pHZ [,] ^t pZH	GND



AC Waveforms





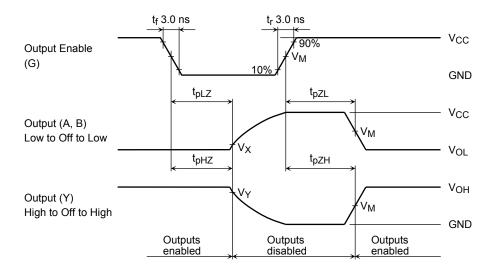


Figure3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

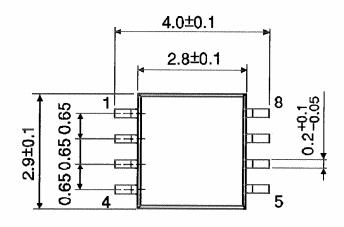
unit	V _{CC}									
unit	3.3±0.3 V	2.5±0.2 V	1.8±0.15 V	1.5±0.1 V	1.2±0.1 V	0.9 V				
VM	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2				
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V	V _{OL} + 0.1 V	V _{OL} + 0.1 V	V _{OL} + 0.1 V				
VY	V _{OH} - 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V	V _{OH} - 0.1 V	V _{OH} - 0.1 V	V _{OH} - 0.1 V				

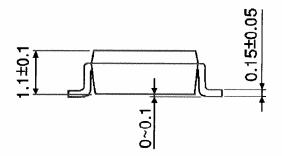
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Package Dimensions

SSOP8-P-0.65

Unit : mm



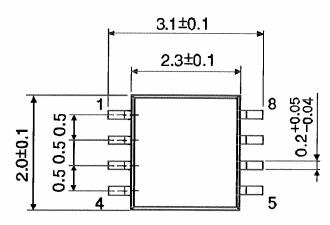


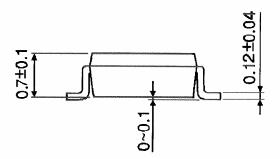
Weight: 0.02 g (typ.)

Package Dimensions

SSOP8-P-0.50A

Unit : mm





Weight: 0.01 g (typ.)

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20070701-EN GENERAL

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